

2. (Amended) A system for processing a semiconductor device, the system comprising:
- a processing chamber; and
 - a first plate positioned within said processing chamber and defining a first internal cavity configured to receive a first gas through a first passage into said first internal cavity at a first temperature and to emit said first gas from said first internal cavity at a second temperature through a second passage; and
 - a second plate disposed adjacent to said first plate, wherein said second plate defines a second internal cavity configured to receive a second gas through a first passage into said second internal cavity at a first temperature and to emit said gas from said second internal cavity at a second temperature through a second passage.
3. (Amended) The system of Claim 2, wherein said second passage comprise a plurality of holes defined on a surface of said first and said second plates.
4. (Amended) The system of Claim 2, wherein said first plate and said second plate comprise a heat source for heating said plate to a preselected temperature.
5. (Amended) The system of Claim 2, wherein said first gas is taken from the group consisting of N₂, He, H₂, O₂, Ar and gas mixtures containing He, H₂, O₂, Ar and N₂.
6. (Amended) The system of Claim 2, wherein said internal cavity further comprises a buffer to disperse said first gas throughout said internal cavity.
7. (Amended) A system for wafer processing comprising:
- a chamber; and
 - at least one heatable plate positionable within said chamber, including:
 - an internal cavity defining an internal wall and configured to receive a gas at a first temperature;
 - means for heating said internal wall to a preselected temperature; and
 - an outlet portion defining a plurality of holes for emitting said gas at a second temperature.

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8. (Amended) A system for wafer processing comprising:
a chamber; and
at least one heatable plate positionable within said chamber, including:
an internal cavity defining an internal wall and configured to receive a gas;
means for heating said internal wall to a preselected temperature; and
an outlet portion defining a plurality of holes for emitting said gas; said at least
one heatable plate including a first heatable plate and a second heatable plate disposed
having adjacent surfaces configured to receive a wafer therebetween.

9. (Amended) The system of Claim 8, wherein said gas is taken from the
group consisting of He, H₂, O₂, Ar, N₂ and gas mixtures containing He, H₂, O₂, Ar,
and N₂.

10. (Amended) The system of Claim 8, wherein said internal cavity further
comprises a buffer to disperse said first gas throughout said internal cavity.

Please cancel Claims 11 and 12.

Please add new Claims 13-16.

--13. (New) The system of Claim 1, wherein said first gas is taken from the
group consisting of N₂, He, H₂, O₂, Ar and gas mixtures containing He, H₂, O₂, Ar and
N₂.

14. (New) The system of Claim 1, wherein said internal cavity further
comprises a buffer to disperse said first gas throughout said internal cavity.

15. (New) The system of Claim 7, wherein said gas is taken from the group
consisting of He, H₂, O₂, Ar, N₂ and gas mixtures containing He, H₂, O₂, Ar, and N₂.

16. (New) The system of Claim 7, wherein said internal cavity further
comprises a buffer to disperse said first gas throughout said internal cavity.--

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